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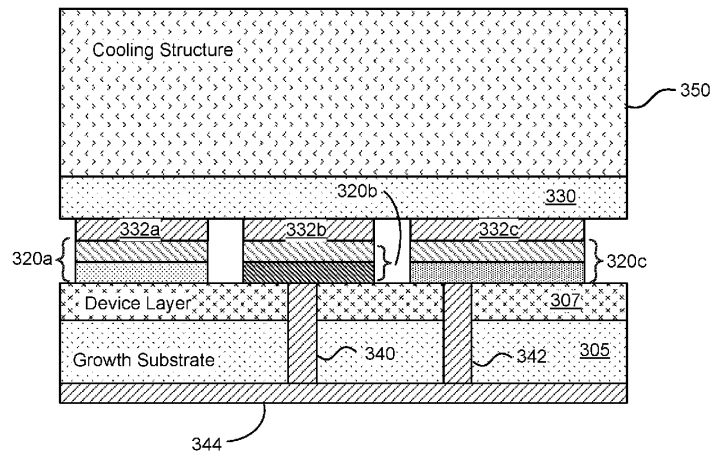


FIG. 3G

(57) Abstract: A monolithic microwave integrated circuit (MMIC) system includes a growth substrate, a device layer coupled to the growth substrate, a plurality of MMIC device elements coupled to the device layer, and a plurality of metallization structures coupled to the plurality of MMIC device elements. The MMIC system also includes a carrier substrate coupled to the plurality of metallization structures and a cooling structure coupled to the carrier substrate.

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